

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Keiji HOSOTANI

SERIAL NO: NEW DIVISIONAL APPLICATION

GAU:

FILED: HEREWITH

EXAMINER:

FOR: SEMICONDUCTOR MEMORY DEVICE UTILIZING TUNNEL MAGNETO RESISTIVE EFFECTS AND
METHOD FOR MANUFACTURING THE SAME

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

The applicant(s) wishes to make of record the references listed on the attached PTO-1449 form. Copies of the listed references were made of record in parent application serial no. 10/225,247, filed August 22, 2002, as were either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.

A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.

A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.

No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLOJ, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.



Eckhard H. Kuesters

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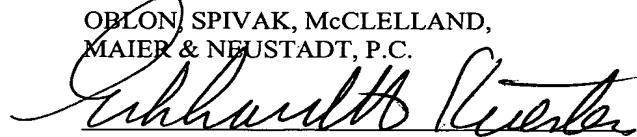
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Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 247252US2S DIV		SERIAL NO. New Div. Application	
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Keiji HOSOTANI					
		FILING DATE HEREWITH		GROUP			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	6,072,718	06/06/00	ABRAHAM ET AL			
	AB	2001/0035545	11/01/01	SCHUSTER-WOLDAN ET AL			
	AC	5,936,882	08/10/99	DUNN			
	AD	6,048,739	04/11/02	HURST ET AL			
	AE	6,278,631	08/21/01	NAJI			
	AF	5,883,828	03/16/99	CUCHIARO ET AL			
	AG	2002/0039308	04/04/2002	GOGL ET AL			
	AH	6,522,573	02-2003	SAITO ET AL			
	AI	6,421,271	07-2002	GOGI ET AL			
	AJ	6,211,559	04-2001	ZHU ET AL			
	AK	6,538,297	03-2003	ODAGAWA ET AL			
	AL	6,365,419	04/02/02	DURLAM ET AL			
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
	AO	2001-357666	12/26/01	JAPAN	YES	NO	X
	AP	2001-217398	08/10/01	JAPAN (w/ENGLISH ABSTRACT)			X
	AQ	2002-157874	05/31/02	JAPAN (w/ENGLISH ABSTRACT)			x
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AW	Roy SCHEUERLEIN, et al., "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell", ISCC 2000/SESSION 7/TD: EMERGING MEMORY & DEVICE TECHNOLOGIES/PAPER TA 7.2, 2000 IEEE International Solid-State Circuits Conference, February 8, 2000, pgs. 126-133.					
	AX	Peter K. NAJI, et al., "A 256kb 3.0V 1T1MTJ Nonvolatile Magnetoresistive RAM", ISSCC 2001/SESSION 7/TECHNOLOGY DIRECTIONS: ADVANCED TECHNOLOGIES/7.6, TECHNOLOGY DIGEST, 2001 IEEE International Solid-State Circuits Conference, 11 pgs.					
	AY						
	AZ					<input type="checkbox"/> Additional References sheet(s) attached	
Examiner				Date Considered			

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.